

**PNP SILICON PLANAR EXPITAXIAL TRANSISTOR.**

**2N4037**



**TO-39  
Metal Can Package**

**MEDIUM POWER AMPLIFIER AND SWITCHING APPLICATIONS.**

**ABSOLUTE MAXIMUM RATINGS (Ta=25°C unless specified otherwise)**

DESCRIPTION	SYMBOL	VALUE	UNITS
Collector Emitter Voltage	$V_{CEO(sus)}$ *	40	V
Collector Base Voltage	$V_{CBO}$	60	V
Emitter Base Voltage	$V_{EBO}$	7.0	V
Collector Current Continuous	$I_C$	1.0	A
Base Current	$I_B$	0.5	A
Continuous Power Dissipation @ or Below Ta=25°C	$P_D$	1.0	W
Linear Derating Dissipation		5.72	mW/°C
Operating And Storage Junction Temperature Range	$T_j, T_{stg}$	-65 to +200	°C

\* Must not be tested on a curve tracer.

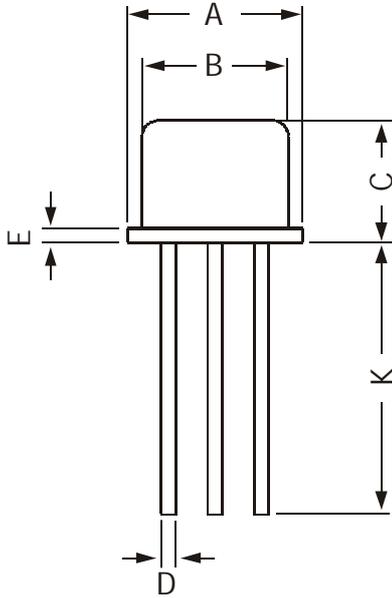
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless specified otherwise)**

DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
Collector Emitter sustaining Voltage	$V_{(BR)CEO(sus)}$	$I_C=100mA, I_B=0$	>40	V
Collector Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	>60	V
Collector Cut off Current	$I_{CBO}$	$V_{CB}=60V, I_E=0$	<250	nA
Emitter Cut off Current	$I_{EBO}$	$V_{BE}=5V, I_C=0$	<20	nA
DC Current Gain	hFE	$I_C=1mA, V_{CE}=10V$	>15	
		$I_C=150mA, V_{CE}=10V$	50-250	
Collector Emitter (sat) Voltage	$V_{CE(Sat)}$	$I_C=150mA, I_B=15mA$	<1.4	V
Base Emitter Voltage	$V_{BE(On)}$	$I_C=150mA, V_{CE}=10V$	<1.5	V

**DYNAMIC CHARACTERISTICS**

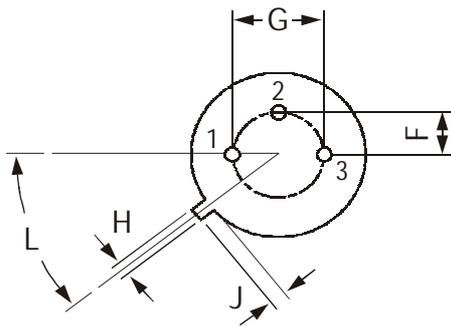
DESCRIPTION	SYMBOL	TEST CONDITION	VALUE	UNITS
Collector Base Capacitance	$C_{cb}$	$V_{CB}=10V, f=20MHz$	<30	pF
Current Gain -High Frequency	$ h_{fe} $	$I_C=50mA, V_{CE}=10V, f=20MHz$	3.0-1.0	

TO-39 Metal Can Package



All dimensions are in mm

DIM	MIN	MAX
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	—	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	—
L	42 DEG	48 DEG



- PIN CONFIGURATION
1. EMITTER
  2. BASE
  3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-39	500 pcs/polybag	540 gm/500 pcs	3" x 7.5" x 7.5"	20K	17" x 15" x 13.5"	32K	40 kgs

### **Disclaimer**

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